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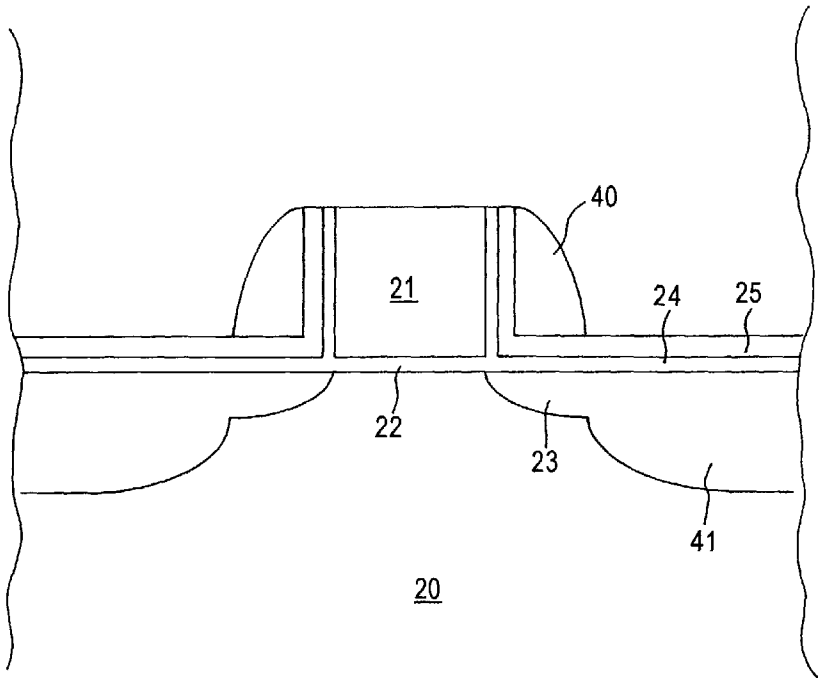
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(54) Title: COMPOSITE SPACER LINER FOR IMPROVED TRANSISTOR PERFORMANCE



(57) Abstract: Semiconductor devices with improved transistor performance are fabricated by forming a composite oxide/nitride liner (24,25) under a gate electrode sidewall spacer (40). Embodiements include depositing a conformal oxide layer (24) by decoupled plasma deposition, depositing a conformal nitride layer (25) by decoupled plasma deposition, depositing a spacer layer (30) and then etching.

WO 03/054952 A1

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